

**IN THE SPECIFICATION:**

Please replace paragraph [0012] with the following amended paragraph:

The inventors are now proposing to install a new ion gauge to an ion implanter such as AXCELIS GSD™ platform implanters. The new ion gauge may be installed in the process chamber. The new ion gauge may be advantageous for implants such as nitrogen, which produce similar pressure responses, such as significantly below  $1 \times 10^{-4}$ . However, for more conventional implants, the pressure is too high to be accurately sensed by the new ion gauge. For example, conventional implants such as arsenic produce pressures greater than  $1.0 \times 10^{-4}$  Torr. A single ion gauge cannot effectively be used for both implants. For this reason, it is desirable for the implanter to be equipped with both a conventional gauge and the new, inside-process-chamber ion gauge. However, many conventional ion implanters have only a single gauge controller. Additionally, it is desirable that the implanter should automatically switch between the ion gauges depending on the implanted recipe. Further, it is desirable that the automatic switching be done without excessive expense or time consuming hardware.